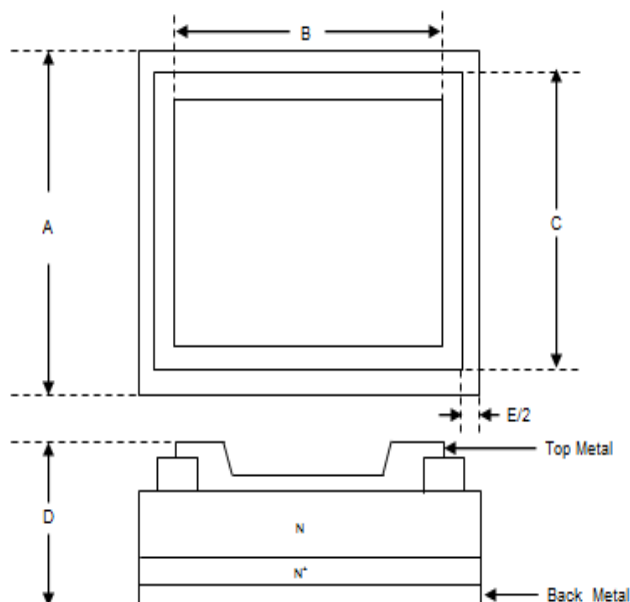


Planar MOS-Controlled Diode Wafer (PMCD)



Item	Dimensions	
	um	mil
Die Size (A)	2220	87
Top Metal Pad Size (B)	1990	78.3
Passivation Seal (C)	2150	84.6
Wafer Thickness (D)	260	10.2
Scribe Line Width (E)	70	2.76
Other Informations		
Wafer Size	6"	
Gross Die	3230	
Top Metal	Ag	
Back Metal	Ag	

Electrical Characteristics @TA=25°C				
Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.3mA	V_{RRM}	45	51	V
Maximum Average Forward Rectified Current	I_O	10	-	A
Forward Voltage Drop, @ $I_F=2A$ @ $I_F=5A$ @ $I_F=10A$	V_F	- 0.44 0.49	0.36 - -	V
Maximum Reverse Current at Rated V_{RRM}	I_R	120	100	μA
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	180	-	A
Operating Temperature Range	T_J	-50 to +150	-	°C
Storage Temperature Range	T_{STG}	-50 to +150	-	°C
ESD(IEC61000-4-2)	Contact	18	-	KV